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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	15
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 6x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1007adna-w0

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RL78/G13 1. OUTLINE

Table 1-1. List of Ordering Part Numbers

(9/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
64 pins	64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)	Mounted	A	R5F100LCAFB#V0, R5F100LDAFB#V0, R5F100LEAFB#V0, R5F100LFAFB#V0, R5F100LGAFB#V0, R5F100LHAFB#V0, R5F100LJAFB#V0, R5F100LKAFB#V0, R5F100LCAFB#X0, R5F100LDAFB#X0, R5F100LEAFB#X0, R5F100LFAFB#X0, R5F100LFAFB#X0, R5F100LJAFB#X0, R5F100LJAFB#X0, R5F100LJAFB#X0, R5F100LJAFB#X0, R5F100LJAFB#X0, R5F100LLAFB#X0
			D	R5F100LCDFB#V0, R5F100LDDFB#V0, R5F100LEDFB#V0, R5F100LFDFB#V0, R5F100LFDFB#V0, R5F100LHDFB#V0, R5F100LJDFB#V0, R5F100LJDFB#V0, R5F100LDFB#V0 R5F100LCDFB#X0, R5F100LDDFB#X0, R5F100LEDFB#X0, R5F100LFDFB#X0, R5F100LFDFB#X0, R5F100LJDFB#X0, R5F100LJDFB#X0, R5F100LJDFB#X0, R5F100LLDFB#X0
			G	R5F100LCGFB#V0, R5F100LDGFB#V0, R5F100LEGFB#V0, R5F100LFGFB#V0 R5F100LCGFB#X0, R5F100LDGFB#X0, R5F100LEGFB#X0, R5F100LFGFB#X0 R5F100LGGFB#V0, R5F100LHGFB#V0, R5F100LJGFB#V0
				R5F100LGGFB#X0, R5F100LHGFB#X0, R5F100LJGFB#X0
		Not mounted	A	R5F101LCAFB#V0, R5F101LDAFB#V0, R5F101LEAFB#V0, R5F101LFAFB#V0, R5F101LGAFB#V0, R5F101LHAFB#V0, R5F101LJAFB#V0, R5F101LKAFB#V0, R5F101LCAFB#X0, R5F101LDAFB#X0, R5F101LEAFB#X0,
			D	R5F101LFAFB#X0, R5F101LGAFB#X0, R5F101LHAFB#X0, R5F101LJAFB#X0, R5F101LKAFB#X0, R5F101LLAFB#X0 R5F101LCDFB#V0, R5F101LDDFB#V0, R5F101LEDFB#V0, R5F101LFDFB#V0, R5F101LFDFB#V0, R5F101LJDFB#V0, R5F101LJDFB#V0, R5F101LLDFB#V0, R5F101LCDFB#X0,
				R5F101LFDFB#X0, R5F101LGDFB#X0, R5F101LHDFB#X0, R5F101LJDFB#X0, R5F101LKDFB#X0, R5F101LLDFB#X0
	64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)	Mounted	A	R5F100LCABG#U0, R5F100LDABG#U0, R5F100LEABG#U0, R5F100LFABG#U0, R5F100LGABG#U0, R5F100LHABG#U0, R5F100LJABG#U0 R5F100LCABG#W0, R5F100LDABG#W0, R5F100LEABG#W0,
	picity		G	R5F100LFABG#W0, R5F100LGABG#W0, R5F100LHABG#W0, R5F100LJABG#W0 R5F100LCGBG#U0, R5F100LDGBG#U0, R5F100LEGBG#U0, R5F100LFGBG#U0, R5F100LGGBG#U0, R5F100LHGBG#U0, R5F100LJGBG#U0
				R5F100LCGBG#W0, R5F100LDGBG#W0, R5F100LEGBG#W0, R5F100LFGBG#W0, R5F100LGGBG#W0, R5F100LHGBG#W0, R5F100LJGBG#W0
		Not mounted	A	R5F101LCABG#U0, R5F101LDABG#U0, R5F101LEABG#U0, R5F101LFABG#U0, R5F101LGABG#U0, R5F101LHABG#U0, R5F101LJABG#U0 R5F101LCABG#W0, R5F101LCABG#W0, R5F101LEABG#W0, R5F101LEABG#W0, R5F101LEABG#W0, R5F101LEABG#W0, R5F101LEABG#W0
				R5F101LFABG#W0, R5F101LGABG#W0, R5F101LHABG#W0, R5F101LJABG#W0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

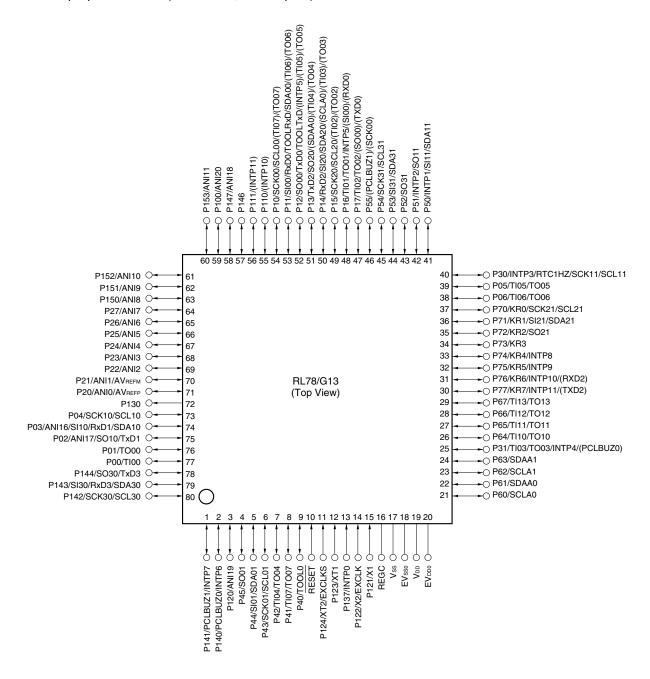
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



RL78/G13 1. OUTLINE

#### 1.3.12 80-pin products

- 80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)
- 80-pin plastic LFQFP (12 x 12 mm, 0.5 mm pitch)



- Cautions 1. Make EVsso pin the same potential as Vss pin.
  - 2. Make VDD pin the potential that is higher than EVDDO pin.
  - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
  - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V<sub>DD</sub> and EV<sub>DD0</sub> pins and connect the Vss and EV<sub>SS0</sub> pins to separate ground lines.
  - **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register** (**PIOR**) in the RL78/G13 User's Manual.

RL78/G13 1. OUTLINE

[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

	Itam	90	nin	100	nin	100	(1/Z)				
	Item	80- R5F100Mx	R5F101Mx	R5F100Px	-pin R5F101Px	128 R5F100Sx	R5F101Sx				
Code flash me	emory (KB)		512		o 512		o 512				
Data flash me	- , ,	8	=	8	=	8	=				
RAM (KB)		8 to 3	2 Note 1	8 to 3	2 Note 1	16 to 3	32 Note 1				
Address spac	е	1 MB		1							
Main system clock	High-speed system clock	HS (High-speed HS (High-speed LS (Low-speed	I main) mode: 1 I main) mode: 1 main) mode: 1	external main sys to 20 MHz (V <sub>DD</sub> = to 16 MHz (V <sub>DD</sub> = to 8 MHz (V <sub>DD</sub> = to 4 MHz (V <sub>DD</sub> =	= 2.7 to 5.5 V), = 2.4 to 5.5 V), 1.8 to 5.5 V),	(EXCLK)					
	High-speed on-chip oscillator	HS (High-speed LS (Low-speed	l main) mode: 1 main) mode: 1	to 32 MHz (V <sub>DD</sub> = to 16 MHz (V <sub>DD</sub> = to 8 MHz (V <sub>DD</sub> = to 4 MHz (V <sub>DD</sub> =	= 2.4 to 5.5 V), 1.8 to 5.5 V),						
Subsystem cl	ock	XT1 (crystal) os 32.768 kHz	cillation, externa	l subsystem cloc	k input (EXCLKS	5)					
Low-speed or	n-chip oscillator	15 kHz (TYP.)									
General-purpo	ose register	(8-bit register × 8) × 4 banks									
Minimum insti	ruction execution time	0.03125 μs (Hig	h-speed on-chip	oscillator: fiн = 3	2 MHz operation	)					
		0.05 μs (High-speed system clock: f <sub>MX</sub> = 20 MHz operation)									
		30.5 $\mu$ s (Subsystem clock: fsub = 32.768 kHz operation)									
Instruction se	t	<ul> <li>Data transfer (8/16 bits)</li> <li>Adder and subtractor/logical operation (8/16 bits)</li> <li>Multiplication (8 bits × 8 bits)</li> <li>Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.</li> </ul>									
I/O port	Total	7	'4	9	92	1	20				
	CMOS I/O	(N-ch O.D. I/O	64 [EV <sub>DD</sub> withstand e]: 21)	(N-ch O.D. I/O	32 [EV <sub>DD</sub> withstand je]: 24)	(N-ch O.D. I/O	10 [EV <sub>DD</sub> withstand e]: 25)				
	CMOS input	!	5		5		5				
	CMOS output		1		1		1				
	N-ch O.D. I/O (withstand voltage: 6 V)		4		4		4				
Timer	16-bit timer	12 cha	annels	12 cha	annels	16 cha	annels				
	Watchdog timer	1 cha	ınnel	1 cha	annel	1 cha	annel				
	Real-time clock (RTC)	1 cha	nnel	1 cha	annel	1 cha	annel				
	12-bit interval timer (IT)	1 cha	nnel	1 cha	annel	1 cha	annel				
	Timer output	12 channels (PWM outputs:	10 Note 2)	12 channels (PWM outputs:	10 Note 2)	16 channels (PWM outputs:	14 <sup>Note 2</sup> )				
	RTC output	1 channel • 1 Hz (subsyst	em clock: fsub =	32.768 kHz)							

**Notes 1.** The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).

Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Iон1 Per pin		P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	<b>І</b> ОН2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo <sub>L1</sub>	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	lo <sub>L2</sub>	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +85	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

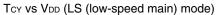
**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

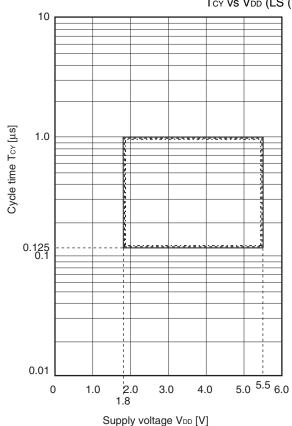
### (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

## (Ta = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V) (1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	I <sub>DD1</sub>	Operating	HS (high-	fin = 32 MHz <sup>Note 3</sup>	Basic	V <sub>DD</sub> = 5.0 V		2.3		mA
Current Note 1		mode	speed main) mode Note 5		operation	V <sub>DD</sub> = 3.0 V		2.3		mA
			modo		Nomal	V <sub>DD</sub> = 5.0 V		5.2	8.5	mA
					operation	V <sub>DD</sub> = 3.0 V		5.2	8.5	mA
				fin = 24 MHz Note 3	Nomal	V <sub>DD</sub> = 5.0 V		4.1	6.6	mA
					operation	V <sub>DD</sub> = 3.0 V		4.1	6.6	mA
				fin = 16 MHz <sup>Note 3</sup>	Normal	V <sub>DD</sub> = 5.0 V		3.0	4.7	mA
					operation	V <sub>DD</sub> = 3.0 V		3.0	4.7	mA
			LS (low-	f <sub>IH</sub> = 8 MHz <sup>Note 3</sup>	Normal	V <sub>DD</sub> = 3.0 V		1.3	2.1	mA
			speed main) mode Note 5		operation	V <sub>DD</sub> = 2.0 V		1.3	2.1	mA
			LV (low-	fin = 4 MHz Note 3	Nomal	V <sub>DD</sub> = 3.0 V		1.3	1.8	mA
			voltage main) mode Note 5		operation	V <sub>DD</sub> = 2.0 V		1.3	1.8	mA
			HS (high- speed main) mode Note 5	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal operation	Square wave input		3.4	5.5	mA
				V <sub>DD</sub> = 5.0 V		Resonator connection		3.6	5.7	mA
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.4	5.5	mA
				V <sub>DD</sub> = 3.0 V	operation	Resonator connection		3.6	5.7	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		2.1	3.2	mA
			V <sub>DD</sub> = 5.0 V	operation	Resonator connection		2.1	3.2	mA	
		LS (low-		$f_{MX} = 10 \text{ MHz}^{Note 2},$	Nomal	Square wave input		2.1	3.2	mA
				V <sub>DD</sub> = 3.0 V	operation	Resonator connection		2.1	3.2	mA
			LS (low- speed main) mode Note 5	$f_{MX} = 8 MHz^{Note 2},$	Normal operation	Square wave input		1.2	2.0	mA
				V <sub>DD</sub> = 3.0 V		Resonator connection		1.2	2.0	mA
				$f_{MX} = 8 MHz^{Note 2}$	Normal	Square wave input		1.2	2.0	mA
				V <sub>DD</sub> = 2.0 V	operation	Resonator connection		1.2	2.0	mA
			Subsystem	fsub = 32.768 kHz	Nomal	Square wave input		4.8	5.9	μA
			clock operation	T <sub>A</sub> = -40°C	operation	Resonator connection		4.9	6.0	μΑ
				fsub = 32.768 kHz	Normal	Square wave input		4.9	5.9	μA
				T <sub>A</sub> = +25°C	operation	Resonator connection		5.0	6.0	μΑ
				fsuB = 32.768 kHz	Normal	Square wave input		5.0	7.6	μΑ
				Note 4	operation	Resonator connection		5.1	7.7	μΑ
				T <sub>A</sub> = +50°C	Nies 1	0		<b>5</b> 0	0.0	
				fsub = 32.768 kHz	Normal operation	Square wave input		5.2	9.3	μA
				T <sub>A</sub> = +70°C	Sporador1	Resonator connection		5.3	9.4	μΑ
				fsub = 32.768 kHz	Normal	Square wave input		5.7	13.3	μA
				T <sub>A</sub> = +85°C	operation	Resonator connection		5.8	13.4	μA

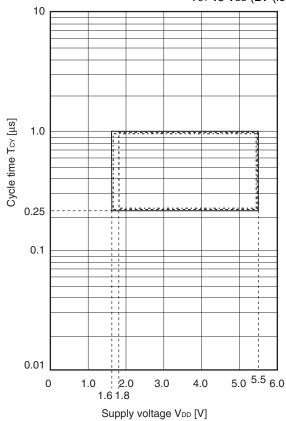
(Notes and Remarks are listed on the next page.)





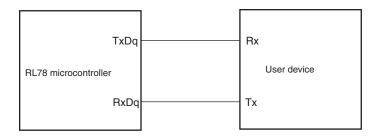
- When the high-speed on-chip oscillator clock is selected
- During self programming
   When high-speed system clock is selected

#### Tcy vs Vdd (LV (low-voltage main) mode)

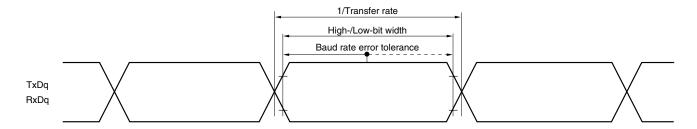


- When the high-speed on-chip oscillator clock is selected During self programming
- --- When high-speed system clock is selected

#### **UART** mode connection diagram (during communication at same potential)



## UART mode bit width (during communication at same potential) (reference)



**Remarks 1.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10 to 13))

220

220

## (4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ Parameter Symbo Conditions HS (high-speed LS (low-speed main) LV (low-voltage main) Unit main) Mode ı Mode Mode MIN. MIN. MAX. MIN. MAX. MAX. Slp setup time tsik2  $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$  $1/f_{MCK}+2$ 1/fmck+30 1/fmck+30 ns (to SCKp↑) Note 1 n  $1.8~V \leq EV_{DD0} \leq 5.5~V$ 1/fмск+3 1/fмск+30 1/fмcк+30 ns 0  $1.7~V \leq EV_{DD0} \leq 5.5~V$ 1/fмск+4  $1/f_{MCK}+40$  $1/f_{MCK}+40$ ns 0 1/fмск+40 1/fмск+40  $1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$ ns Slp hold time tks12  $1.8~V \leq EV_{DD0} \leq 5.5~V$ 1/fмск+3 1/fмcк+31 1/fмcк+31 ns (from SCKp↑) 1  $1.7~V \leq EV_{DD0} \leq 5.5~V$ 1/fмcк+ 1/fмск+ 1/fмcк+ ns 250 250 250  $1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$ 1/fmck+ 1/fмcк+ ns 250 250 2/f<sub>MCK+</sub> 2/f<sub>MCK+</sub> Delay time tks02 C = 30 $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fmck+ ns pF Note 4 from SCKp↓ to 44 110 110 SOp output Note  $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fmck+ 2/fмcк+ 2/fmck+ ns 110 75 110 2/fмск+  $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fмск+ 2/fмск+ ns 110 110 110  $1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fmck+ 2/fmck+ 2/fмск+ ns 220 220 220  $1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fмск+ 2/fмск+ ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to  $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - 4. C is the load capacitance of the SOp output lines.
  - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)
  - 2. fmck: Serial array unit operation clock frequency

    (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

    n: Channel number (mn = 00 to 03, 10 to 13))

## (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	` `	h-speed Mode	`	/-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsıĸı	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $	81		479		479		ns
		$C_b = 30$ pF, $R_b = 1.4$ k $\Omega$							
			177		479		479		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$ \begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array} $	479		479		479		ns
		$C_b = 30$ pF, $R_b = 5.5$ k $\Omega$							
SIp hold time (from SCKp↑) Note 1	<b>t</b> KSI1	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$	19		19		19		ns
		$C_b = 30$ pF, $R_b = 5.5$ k $\Omega$							
Delay time from SCKp↓ to	tkso1	$ \begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array} $		100		100		100	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, $		195		195		195	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$		483		483		483	ns
		$C_b = 30$ pF, $R_b = 5.5$ k $\Omega$							

Notes

- 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 2. Use it with  $EV_{DD0} \ge V_b$ .

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

### 2.6 Analog Characteristics

#### 2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = VBGR
Input channel	Reference voltage (–) = AVREFM	Reference voltage (-) = Vss	Reference voltage (–) = AVREFM
ANI0 to ANI14	Refer to <b>2.6.1 (1)</b> .	Refer to <b>2.6.1 (3)</b> .	Refer to <b>2.6.1 (4)</b> .
ANI16 to ANI26	Refer to <b>2.6.1 (2)</b> .		
Internal reference voltage	Refer to <b>2.6.1 (1)</b> .		_
Temperature sensor output			
voltage			

(1) When reference voltage (+)= AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V  $\leq$  AVREFP  $\leq$  VDD  $\leq$  5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error <sup>Note 1</sup>	AINL	10-bit resolution	1.8 V ≤ AV <sub>REFP</sub> ≤ 5.5 V		1.2	±3.5	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{\text{Note 4}}$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI2 to ANI14	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
			$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μS
		10-bit resolution Target pin: Internal	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
			$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error <sup>Notes 1, 2</sup>	Ezs	10-bit resolution	1.8 V ≤ AV <sub>REFP</sub> ≤ 5.5 V			±0.25	%FSR
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±0.50	%FSR
Full-scale error Notes 1, 2	E <sub>FS</sub>	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±0.25	%FSR
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{REFP} \leq 5.5~V^{\text{Note 4}}$			±0.50	%FSR
Integral linearity error <sup>Note 1</sup>	ILE	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±2.5	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±1.5	LSB
		$AV_{REFP} = V_{DD}^{Note 3}$	$1.6~V \leq AV_{\text{REFP}} \leq 5.5~V^{\text{Note 4}}$			±2.0	LSB
Analog input voltage	VAIN	ANI2 to ANI14		0		AVREFP	V
	Internal reference voltage (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main)				V <sub>BGR</sub> Note 5		V
		Temperature sensor outp (2.4 V $\leq$ VDD $\leq$ 5.5 V, HS	•	\	/TMPS25 Note	5	V

(Notes are listed on the next page.)



 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (4/5)$ 

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V <sub>OH1</sub>	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ loh1 = $-3.0 \text{ mA}$	EV <sub>DD0</sub> – 0.7			V
		to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $I_{\text{OH1}} = -2.0 \text{ mA}$	EV <sub>DD0</sub> – 0.6			V
		P117, P120, P125 to P127, P130, P140 to P147	$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $I_{\text{OH1}} = -1.5 \text{ mA}$	EV <sub>DD0</sub> – 0.5			V
	V <sub>OH2</sub>	P20 to P27, P150 to P156	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH2} = -100 \ \mu \text{ A}$	V <sub>DD</sub> – 0.5			V
Output voltage, low	V <sub>OL1</sub>	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 8.5~mA$			0.7	V
		to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 3.0~mA$			0.6	V
			$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 1.5~mA$			0.4	V
			$2.4~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 0.6~mA$			0.4	٧
	V <sub>OL2</sub>	P20 to P27, P150 to P156	$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $\text{Io}_{L2} = 400 \ \mu \text{ A}$			0.4	V
	Vоьз	P60 to P63	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 15.0~mA$			2.0	V
			$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 5.0~mA$			0.4	V
			$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 3.0~mA$			0.4	V
			$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $\text{Iol3} = 2.0 \text{ mA}$			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

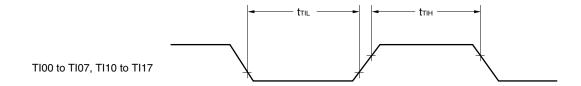
**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

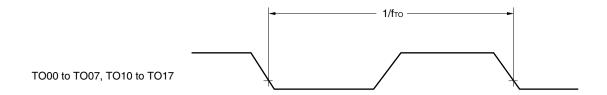
# (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (Ta = -40 to $+105^{\circ}$ C, 2.4 V $\leq$ EV<sub>DD0</sub> = EV<sub>DD1</sub> $\leq$ V<sub>DD</sub> $\leq$ 5.5 V, Vss = EV<sub>SS0</sub> = EV<sub>SS1</sub> = 0 V) (2/2)

Parameter	Symbol		Conditions			MIN.	TYP.	MAX.	Unit
Supply	I <sub>DD2</sub>	HALT	HS (high-	fih = 32 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.62	3.40	mA
Current Note 1	Note 2	mode	speed main) mode Note 7		V <sub>DD</sub> = 3.0 V		0.62	3.40	mA
			mode	fin = 24 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.50	2.70	mA
					V <sub>DD</sub> = 3.0 V		0.50	2.70	mA
				fin = 16 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.44	1.90	mA
					V <sub>DD</sub> = 3.0 V		0.44	1.90	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	2.10	mA
			speed main) mode Note 7	V <sub>DD</sub> = 5.0 V	Resonator connection		0.48	2.20	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	2.10	mA
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.48	2.20	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	1.10	mA
				V <sub>DD</sub> = 5.0 V	Resonator connection		0.28	1.20	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	1.10	mA
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.28	1.20	mA
			Subsystem	fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.28	0.61	μΑ
			clock operation	T <sub>A</sub> = -40°C	Resonator connection		0.47	0.80	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.34	0.61	μΑ
				T <sub>A</sub> = +25°C	Resonator connection		0.53	0.80	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.41	2.30	μΑ
				T <sub>A</sub> = +50°C	Resonator connection		0.60	2.49	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.64	4.03	μΑ
				T <sub>A</sub> = +70°C	Resonator connection		0.83	4.22	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		1.09	8.04	μΑ
				T <sub>A</sub> = +85°C	Resonator connection		1.28	8.23	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		5.50	41.00	μΑ
				T <sub>A</sub> = +105°C	Resonator connection		5.50	41.00	μΑ
	IDD3 <sup>Note 6</sup> STOP TA = -40°	T <sub>A</sub> = -40°C				0.19	0.52	μΑ	
		mode <sup>Note 8</sup>	T <sub>A</sub> = +25°C				0.25	0.52	μΑ
			T <sub>A</sub> = +50°C				0.32	2.21	μΑ
			T <sub>A</sub> = +70°C	T <sub>A</sub> = +70°C				3.94	μΑ
			T <sub>A</sub> = +85°C				1.00	7.95	μΑ
			T <sub>A</sub> = +105°C				5.00	40.00	μΑ

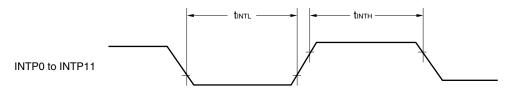
(Notes and Remarks are listed on the next page.)

### **TI/TO Timing**

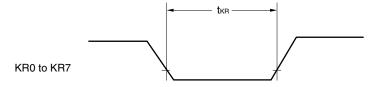




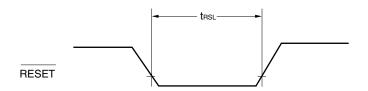
### **Interrupt Request Input Timing**



### **Key Interrupt Input Timing**



## **RESET** Input Timing



## (2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-spee	ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	250		ns
			$2.4~V \leq EV_{DD0} \leq 5.5~V$	500		ns
SCKp high-/low-level width	<b>t</b> кн1,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$ $2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		tkcy1/2 - 24		ns
	t <sub>KL1</sub>			tkcy1/2 - 36		ns
	2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		<sub>00</sub> ≤ 5.5 V	tkcy1/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	tsıĸ1	4.0 V ≤ EV <sub>DD</sub>	<sub>00</sub> ≤ 5.5 V	66		ns
		2.7 V ≤ EV <sub>DD</sub>	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V			ns
		2.4 V ≤ EV <sub>DD</sub>	2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V			ns
SIp hold time (from SCKp↑) Note 2	<b>t</b> KSI1			38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note	o 4		50	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3).
  - g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)
  - 2. fmck: Serial array unit operation clock frequency
    - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
    - n: Channel number (mn = 00 to 03, 10 to 13))

5. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V  $\leq$  EV<sub>DD0</sub> < 3.3 V and 1.6 V  $\leq$  V<sub>b</sub>  $\leq$  2.0 V

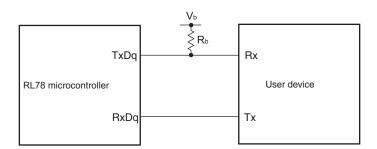
Maximum transfer rate = 
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = 
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{1.5}{V_b})}\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

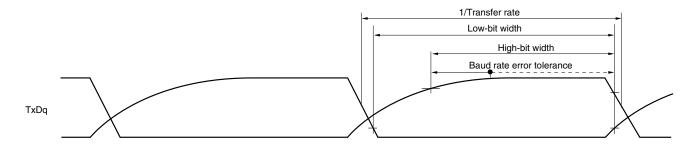
- \* This value is the theoretical value of the relative difference between the transmission and reception sides.
- **6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.

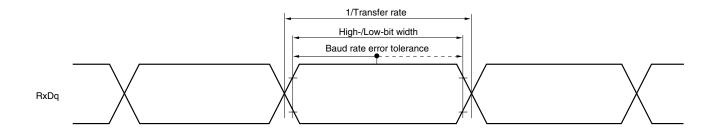
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

**UART** mode connection diagram (during communication at different potential)



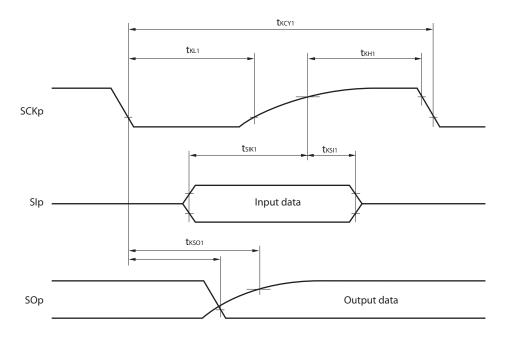
#### UART mode bit width (during communication at different potential) (reference)



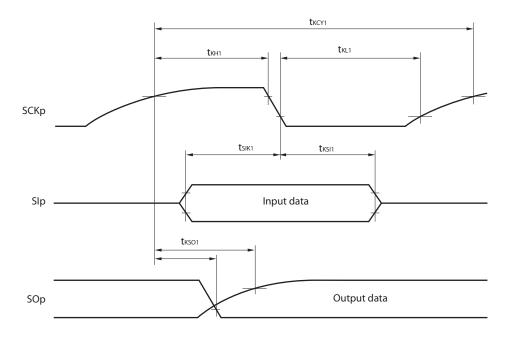


- $\begin{tabular}{ll} \textbf{Remarks 1.} & R_b[\Omega]: Communication line (TxDq) pull-up resistance, \\ & C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage \\ \end{tabular}$ 
  - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
  - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
  - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

# CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



## CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 00, 01, 02, 10, 12, 13), n: Channel number (n = 0, 2), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

**2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

#### 3.5.2 Serial interface IICA

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	HS (h	igh-spee	ed main)	Mode	Unit
				ndard ode	Fast	Fast Mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fclk ≥ 3.5 MHz	-	_	0	400	kHz
		Standard mode: fcLK ≥ 1 MHz	0	100	ı	_	kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μS
Hold time <sup>Note 1</sup>	thd:sta		4.0		0.6		μS
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μS
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μS
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	0.9	μS
Setup time of stop condition	tsu:sto		4.0		0.6		μS
Bus-free time	tBUF		4.7		1.3		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

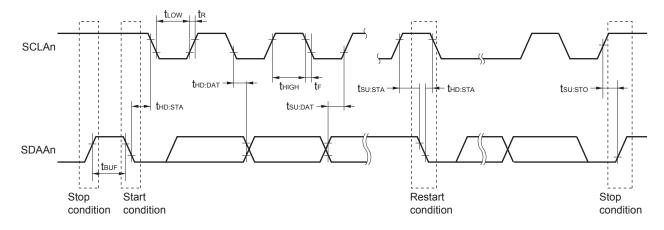
2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

**Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode:  $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode:  $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$ 

#### **IICA** serial transfer timing



Remark n = 0, 1

<R>

### 3.6.5 Power supply voltage rising slope characteristics

#### $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

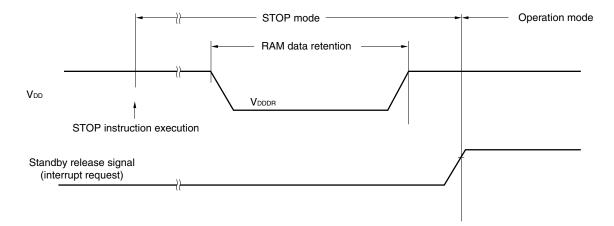
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until  $V_{DD}$  reaches the operating voltage range shown in 3.4 AC Characteristics.

#### 3.7 RAM Data Retention Characteristics

#### $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V <sub>DDDR</sub>		1.44 <sup>Note</sup>		5.5	٧

**Note** This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



		Description		
Rev.	Date	Page	Summary	
3.00	3.00 Aug 02, 2013		Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics	
		118	Modification of table and note in 2.6.3 POR circuit characteristics	
		119	Modification of table in 2.6.4 LVD circuit characteristics	
		120	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode	
		120	Renamed to 2.6.5 Power supply voltage rising slope characteristics	
			Modification of table, figure, and remark in 2.10 Timing Specs for Switching Flash Memory Programming Modes	
		123	Modification of caution 1 and description	
		124	Modification of table and remark 3 in Absolute Maximum Ratings (T <sub>A</sub> = 25°C)	
		126	Modification of table, note, caution, and remark in 3.2.1 X1, XT1 oscillator characteristics	
		126	Modification of table in 3.2.2 On-chip oscillator characteristics	
		127	Modification of note 3 in 3.3.1 Pin characteristics (1/5)	
		128	Modification of note 3 in 3.3.1 Pin characteristics (2/5)	
		133	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (1/2)	
		135	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (2/2)	
		137	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2)	
		139	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2)	
		140	Modification of (3) Peripheral Functions (Common to all products)	
		142	Modification of table in 3.4 AC Characteristics	
		143	Addition of Minimum Instruction Execution Time during Main System Clock Operation	
		143	Modification of figure of AC Timing Test Points	
		143	Modification of figure of External System Clock Timing	
		145	Modification of figure of AC Timing Test Points	
		145	Modification of description, note 1, and caution in (1) During communication at same potential (UART mode)	
		146	Modification of description in (2) During communication at same potential (CSI mode)	
		147	Modification of description in (3) During communication at same potential (CSI mode)	
		149	Modification of table, note 1, and caution in (4) During communication at same potential (simplified I <sup>2</sup> C mode)	
		151	Modification of table, note 1, and caution in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)	
		152 to 154	Modification of table, notes 2 to 6, caution, and remarks 1 to 4 in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)	
		155	Modification of table in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)	
		156	Modification of table and caution in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)	
		157, 158	Modification of table, caution, and remarks 3 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)	
		160, 161	Modification of table and caution in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)	